

C1  
Concl'd

an interlayer insulating film comprising an inorganic material formed on said thin film transistor;

an organic resin film provided over said interlayer insulating film; and

a pixel electrode formed over said organic resin film and connected to said thin film transistor through an opening provided in said organic resin film,

wherein said polycrystalline semiconductor layer exhibits a peak of Raman spectra, displaced from a peak of single crystalline silicon to the lower frequency direction, and

wherein said polycrystalline semiconductor layer is formed by crystallizing an amorphous semiconductor layer.

---

sub D3

19. (Thrice Amended) A semiconductor device comprising:

a first substrate having an insulating surface;

a second substrate opposing said first substrate;

at least one thin film transistor formed on said insulating surface, said thin film transistor comprising:

CA

a polycrystalline semiconductor layer having source, drain and channel regions;

a gate insulating layer adjacent to said channel region; and

a gate electrode adjacent to said channel region;

an interlayer insulating film comprising an inorganic material formed on said thin film transistor; and

an organic resin film provided over said interlayer insulating film;

wherein said polycrystalline semiconductor layer exhibits a peak of Raman spectra, displaced from a peak of single crystalline silicon to the lower frequency direction, and

wherein said polycrystalline semiconductor layer is formed by crystallizing

C2  
Com'd  
an amorphous semiconductor layer.

sub P57  
C3  
45. (Thrice Amended) A semiconductor device comprising:  
a first substrate having an insulating surface;  
a second substrate opposing said first substrate;  
at least an n-channel thin film transistor and at least a p-channel thin film transistor both formed over said first substrate, each of said n-channel and p-channel thin film transistors comprising:  
a polycrystalline semiconductor layer having source, drain and channel regions;  
a gate insulating layer adjacent to said channel region; and  
a gate electrode adjacent to said channel region;  
an interlayer insulating film comprising an inorganic material formed on said thin film transistor; and  
an organic resin film provided over said interlayer insulating film;  
wherein said polycrystalline semiconductor layer exhibits a peak of Raman spectra, displaced from a peak of single crystalline silicon to the lower frequency direction, and  
wherein said polycrystalline semiconductor layer is formed by crystallizing an amorphous semiconductor layer.

#### REMARKS

Applicant would like to thank the Examiner for the consideration given the present application. The Office Action of **October 18, 2001**, has been received and its contents carefully noted. Filed concurrently herewith is a *Request for a One (1) Month Extension of Time* which extends the shortened statutory period for response to **February 18, 2002 (Federal Holiday)**. Accordingly, Applicant respectfully submits that this response is